

Structural variations induced by thermal treatment in lead feldspar ($\text{PbAl}_2\text{Si}_2\text{O}_8$)

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ABSTRACT

Lead feldspar single crystals were annealed at $T = 1050$ and 1000 °C, starting from a disordered metastable configuration (PbF_H , $Q_{\text{od}} = 0$) and from an ordered configuration (PbF_L , $Q_{\text{od}} = 0.89$). Single-crystal data collection and refinement in space group $I2/c$ show that the degree of Al-Si order increases to $Q_{\text{od}} = 0.42$ after annealing the disordered PbF_H at 1050 °C and decreases to $Q_{\text{od}} = 0.70$ after annealing the ordered PbF_L sample at 1000 °C. This suggests that the equilibrium Q_{od} is between 0.70 and 0.42 for temperatures between 1000 and 1050 °C, where anorthite or strontium feldspar are almost completely ordered. A residual in the difference-Fourier map because of positional disorder was observed near the Pb site in all the refined crystals. The average y/b_{pb} coordinate changes with increasing Al-Si disorder, as Pb approaches the glide plane. A significant decrease in the intensity of b -type reflections was consequently observed. A spontaneous strain, with the main axis almost parallel to the a axis, is associated with Al-Si ordering. Pb polyhedral deformation related with Q_{od} accounts for the observed strain. A calibrating equation, $Q_{\text{od}} = [(8.427(2) - a) / 0.048(3)]^{1/2}$, has been calculated and applied to the unit-cell parameters obtained from subsequent thermal treatments and from Bruno and Facchinelli (1972) to define the evolution of the Q_{od} vs. the treatment temperature. The thermal behavior of the Q_{od} could then be bracketed, suggesting T_c between 1150 and 1200 °C for the $I2/c$ - $C2/m$ phase transition induced by the Al-Si order-disorder process.